**Product data sheet** 

# 1. General description

NPN low V<sub>CEsat</sub> transistor in a small SOT23 plastic package. PNP complement: PBSS5140T-Q.

#### 2. Features and benefits

- Low collector-emitter saturation voltage
- High current capabilities
- Improved device reliability due to reduced heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · General purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- · Battery driven equipment (mobile phones, video cameras and hand-held devices).

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	40	V
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	2	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 500 mA; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	260	500	mΩ



40 V, 1 A NPN low VCEsat (BISS) transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		в—Қ
			SOT23	 E sym123

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS4140T-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS4140T-Q	ZT%

[1] % = placeholder for manufacturing site code

40 V, 1 A NPN low VCEsat (BISS) transistor

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	40	V
$V_{CEO}$	collector-emitter voltage	open base		-	40	V
$V_{EBO}$	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	1	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	450	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W	
		[2]	-	-	278	K/W	

Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

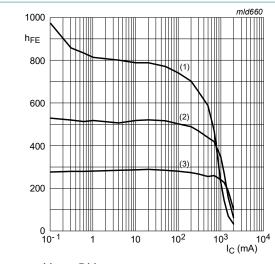
## 40 V, 1 A NPN low VCEsat (BISS) transistor

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	40	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	40	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = 100 μA; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C	300	-	-	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 500 mA; T <sub>amb</sub> = 25 °C	300	-	900	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	200	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 1 mA; T <sub>amb</sub> = 25 °C	-	-	200	mV
	saturation voltage	$I_C$ = 500 mA; $I_B$ = 50 mA; $T_{amb}$ = 25 °C	-	-	250	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; T <sub>amb</sub> = 25 °C	-	-	500	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 500 mA; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	260	500	mΩ
$V_{BEsat}$	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; T <sub>amb</sub> = 25 °C	-	-	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	-	-	1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25  ^{\circ}\text{C}$	-	-	10	pF

#### 40 V, 1 A NPN low VCEsat (BISS) transistor

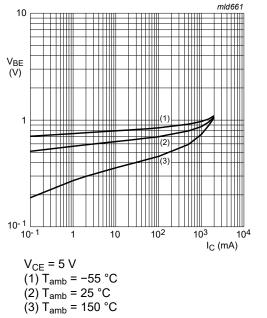


$$V_{CE} = 5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values

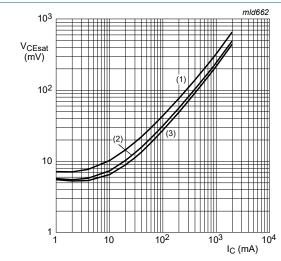


$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 150 °C$$

Base-emitter voltage as a function of collector Fig. 2. current; typical values



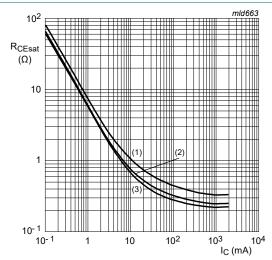
$$I_C/I_B = 10$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \text{ °C}$$
  
(3)  $T_{amb} = -55 \text{ °C}$ 

Fig. 3. Collector-emitter saturation voltage as a function of collector current; typical values



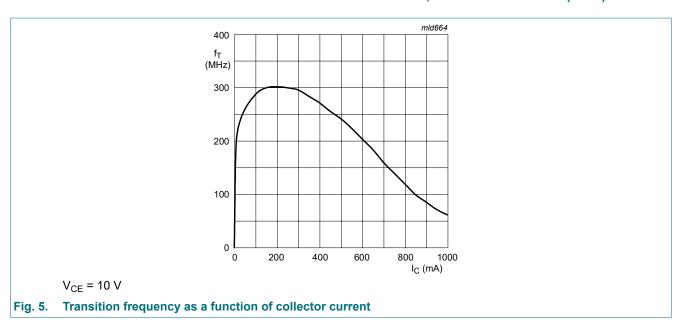
$$I_C/I_B = 10$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Equivalent on-resistance as a function of Fig. 4. collector current; typical values

### 40 V, 1 A NPN low VCEsat (BISS) transistor



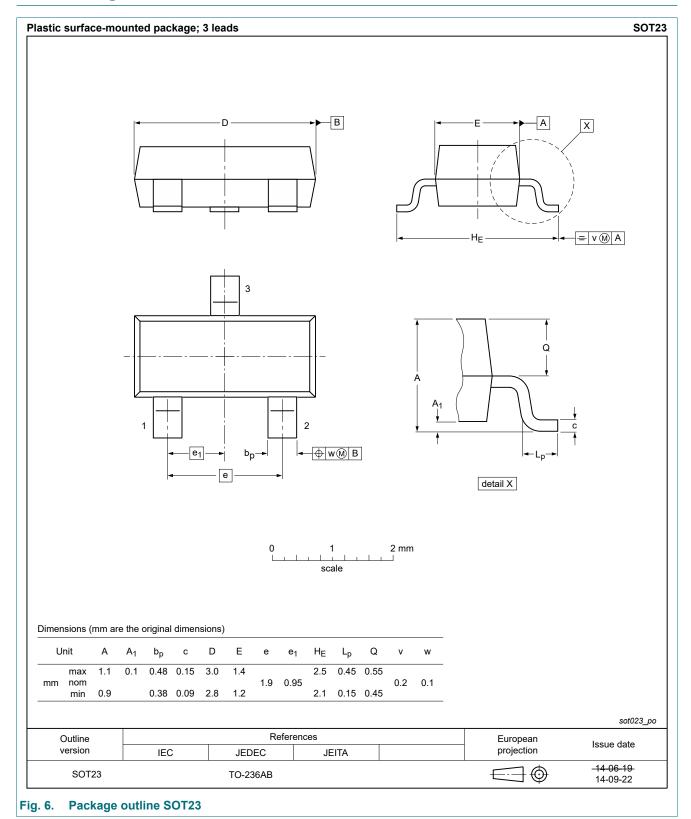
## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

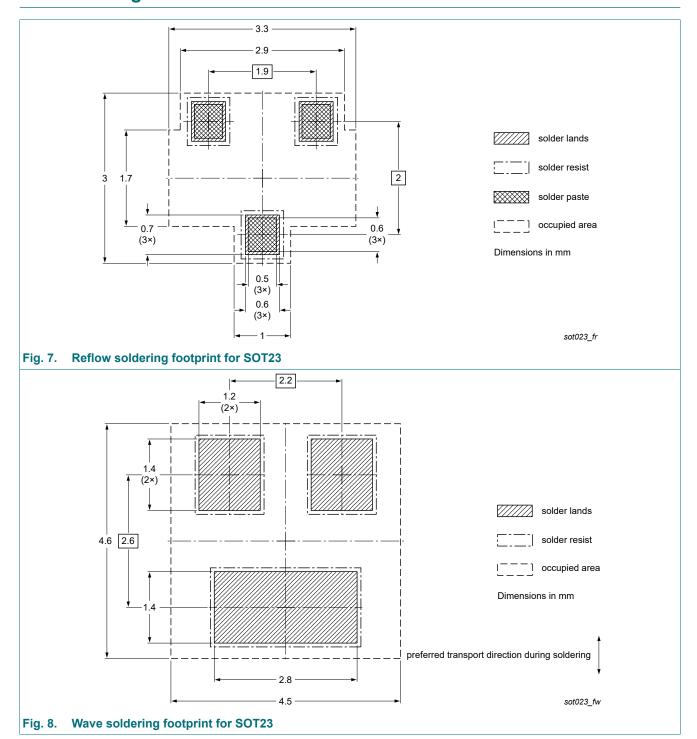
### 40 V, 1 A NPN low VCEsat (BISS) transistor

# 12. Package outline



### 40 V, 1 A NPN low VCEsat (BISS) transistor

# 13. Soldering



40 V, 1 A NPN low VCEsat (BISS) transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4140T-Q v.1	20211215	Product data sheet	-	-

### 40 V, 1 A NPN low VCEsat (BISS) transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 40 V, 1 A NPN low VCEsat (BISS) transistor

## **Contents**

1.	General description	. 1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	. 1
5.	Pinning information	. 2
6.	Ordering information	. 2
7.	Marking	. 2
8.	Limiting values	. 3
9.	Thermal characteristics	. 3
10.	Characteristics	. 4
11.	Test information	. 6
12.	Package outline	. 7
13.	Soldering	. 8
14.	Revision history	.9
	Legal information	

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